

Form PTO-1449



INFORMATION DISCLOSURE CITATION  
IN AN APPLICATION.

(Use several sheets if necessary)

|                            |                    |
|----------------------------|--------------------|
| Document Number (Sequence) | Application Number |
| IME-03-011                 | 10/763,304         |
| Applicant                  |                    |
| Shajan Mathew et al.       |                    |
| Filing Date                | Draw Art Unit      |
| 01/23/04                   |                    |

U. S. PATENT DOCUMENTS

|     | DOCUMENT NUMBER | DATE    | TITLE          | CLASS | SUBCLASS | FILED DATE<br>IF APPROPRIATE |
|-----|-----------------|---------|----------------|-------|----------|------------------------------|
| T.D | 6 4 7 5 8 7 4   | 11/5/02 | Xiang et al.   | 438   | 396      | 12/7/00                      |
|     | 6 5 0 3 8 3 3   | 1/7/03  | Ajmera et al.  | 438   | 682      | 11/15/00                     |
|     | 6 5 3 4 3 9 0   | 3/18/03 | Chang et al.   | 438   | 592      | 1/16/02                      |
|     | 6 4 3 6 8 4 0   | 8/20/02 | Besser et al.  | 438   | 721      | 10/19/00                     |
|     | 6 4 4 0 8 6 8   | 8/27/02 | Besser et al.  | 438   | 721      | 10/19/00                     |
|     | 6 3 2 6 2 5 1   | 12/4/01 | Gardner et al. | 438   | 197      | 1/12/99                      |
|     | 6 0 8 4 2 7 9   | 7/4/00  | Nguyen et al.  | 257   | 412      | 3/31/97                      |
| T.D | 6 4 7 5 9 0 8   | 11/5/02 | Lin et al.     | 438   | 659      | 10/18/01                     |
|     |                 |         |                |       |          |                              |
|     |                 |         |                |       |          |                              |
|     |                 |         |                |       |          |                              |
|     |                 |         |                |       |          |                              |

FOREIGN PATENT DOCUMENTS

|  | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | Translation |    |
|--|-----------------|------|---------|-------|----------|-------------|----|
|  |                 |      |         |       |          | YES         | NO |
|  |                 |      |         |       |          |             |    |
|  |                 |      |         |       |          |             |    |
|  |                 |      |         |       |          |             |    |
|  |                 |      |         |       |          |             |    |
|  |                 |      |         |       |          |             |    |
|  |                 |      |         |       |          |             |    |

OTHER DOCUMENTS (Including Author, Title, Date, Portion of Pages, Etc.)

|     |  |
|-----|--|
| T.D | "High Performance Damascene Metal Gate MOSFET's for 0.1um Regime", IEEE Trans. on Electron Devices, Vol. 47, No. 5, May 200, pp. 1028-1034 by Yagashita et al. |
| T.D | "CMOS Metal Replacement Gate Transistors using Tantalum Pentoxide Gate Insulator", by Chatterjee et al., IEDM 98-777, 29.1.1 to 29.1.4.                        |

|          |                 |
|----------|-----------------|
| EXAMINER | DATE CONSIDERED |
| T. DANG  | 10/25/04        |

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

